

ABSTRACT OF THE DISCLOSURE

Ammonia for use in the manufacture of a GaN-type compound semiconductor, filled in a charging container 18 such that at least a part of the ammonia is liquid and the liquid phase ammonia has a water concentration determined by a Fourier-transform infrared spectroscopy (FT-IR) of 0.5 vol ppm or less, is introduced in the gaseous state into a reaction chamber 11 housing therein a substrate 1, and a layer comprising a GaN-type compound started from this ammonia is formed on the substrate 1.